

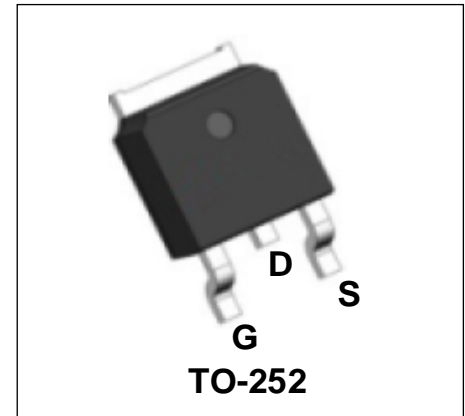
40V P-Channel Enhancement Mode Power MOSFET

Description

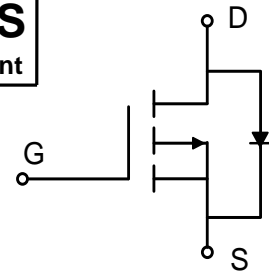
WMO50P04T1 uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Features

- $V_{DS} = -40V$, $I_D = -50A$
 $R_{DS(on)} < 13m\Omega$ @ $V_{GS} = -10V$
 $R_{DS(on)} < 20m\Omega$ @ $V_{GS} = -4.5V$
- Green Device Available
- Low Gate Charge
- Advanced High Cell Density Trench Technology
- 100% EAS Guaranteed



RoHS
compliant



Applications

- Power Management Switches
- DC/DC Converters

Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current@-10V ¹	$T_C = 25^\circ C$	I_D	-50	A
	$T_C = 100^\circ C$		-31	
Pulsed Drain Current ²		I_{DM}	-103	A
Single Pulse Avalanche Energy ³		EAS	72	mJ
Avalanche Current		I_{AS}	-38	A
Total Power Dissipation ⁴	$T_C = 25^\circ C$	P_D	51	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ¹	$R_{\theta JA}$	62.5	$^\circ C/W$
Thermal Resistance from Junction-to-Case ¹	$R_{\theta JC}$	2.45	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-40	-	-	V
Gate-body Leakage current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = -32V, V _{GS} = 0V	-	-	1	μA
	T _J =55°C			-	-	5	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
Drain-Source On-Resistance ²		R _{DS(on)}	V _{GS} = -10V, I _D = -16A	-	11.5	13	mΩ
			V _{GS} = -4.5V, I _D = -12A	-	16	20	
Forward Transconductance ²		g _{fs}	V _{DS} = -5V, I _D = -18A	-	23	-	S
Dynamic Characteristics							
Input Capacitance		C _{iss}	V _{DS} = -20V, V _{GS} =0V, f =1MHz	-	3320	-	pF
Output Capacitance		C _{oss}		-	290	-	
Reverse Transfer Capacitance		C _{rss}		-	225	-	
Switching Characteristics							
Gate Resistance		R _g	V _{DS} = 0V, V _{GS} =0V, f =1MHz	-	3.3	-	Ω
Total Gate Charge		Q _g	V _{GS} = -4.5V,V _{DS} = -20V, I _D = -12A	-	28	-	nC
Gate-Source Charge		Q _{gs}		-	7.8	-	
Gate-Drain Charge		Q _{gd}		-	7.6	-	
Turn-on Delay Time		t _{d(on)}	V _{GS} =-10V, V _{DS} = -15V, R _G = 3.3Ω, I _D = -1A	-	41	-	nS
Rise Time		t _r		-	35.5	-	
Turn-off Delay Time		t _{d(off)}		-	99	-	
Fall Time		t _f		-	9.5	-	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ²		V _{SD}	I _S = -1A, V _{GS} = 0V	-	-	-1	V
Continuous Source Current ^{1,5}		I _S	V _G =V _D =0V , Force Current	-	-	-50	A

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.1\text{mH}, I_{AS} = 38A$
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

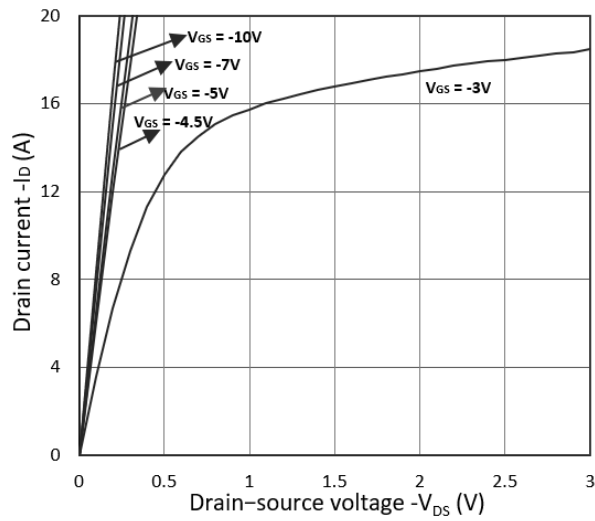


Figure 1. Output Characteristics

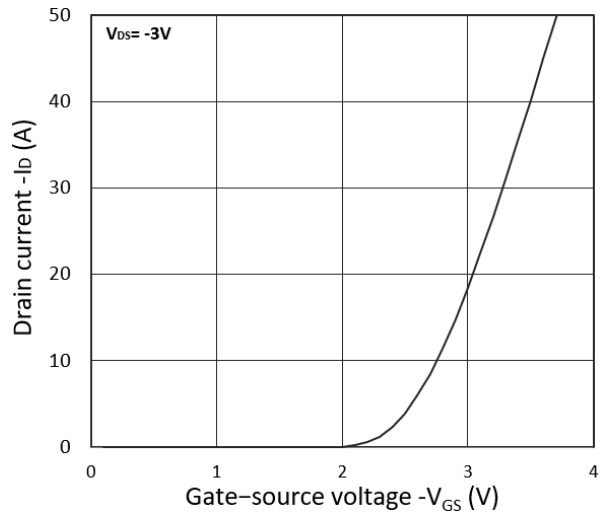


Figure 2. Transfer Characteristics

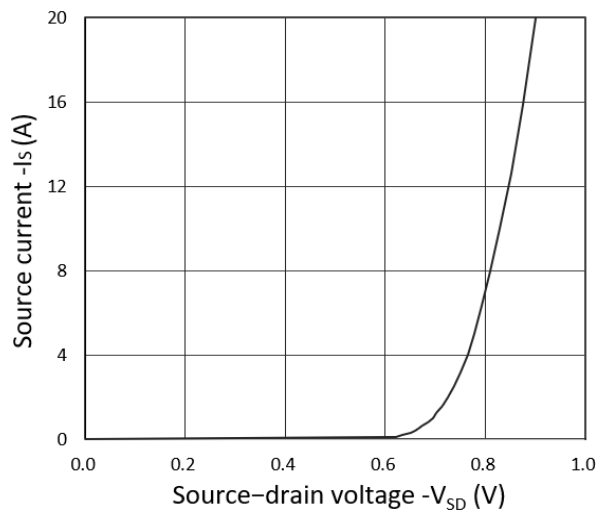


Figure 3. Forward Characteristics of Reverse

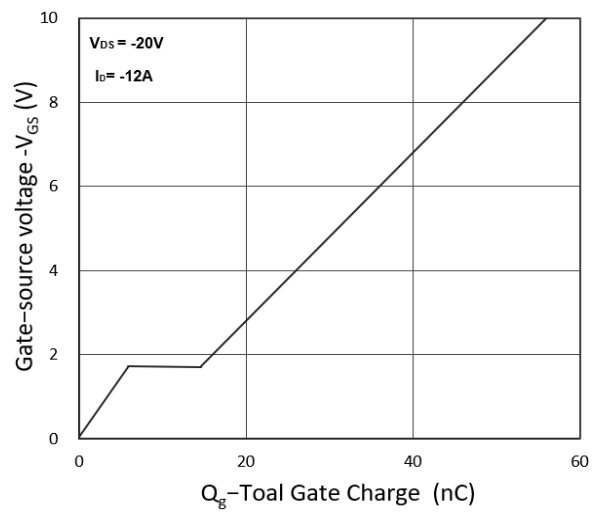
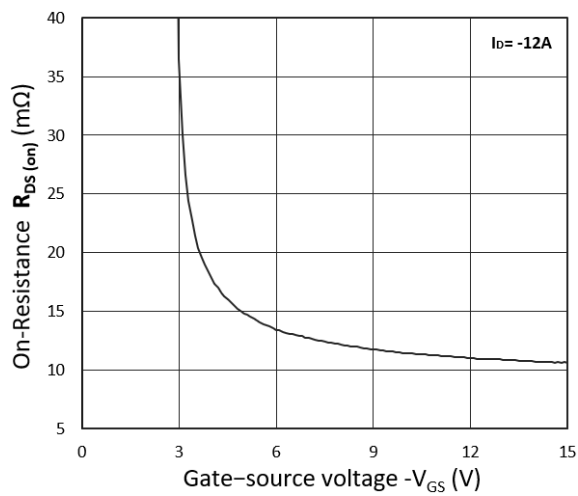
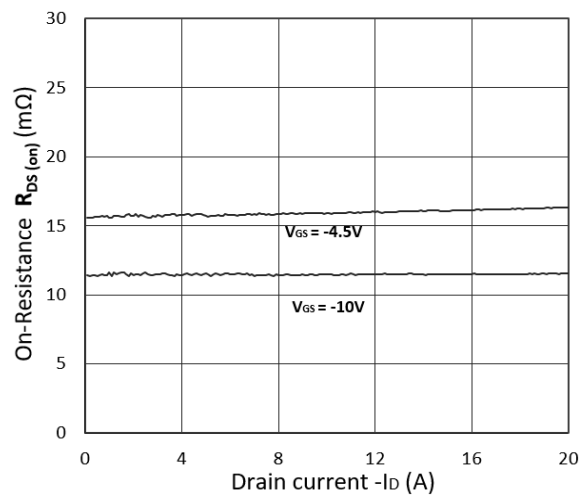


Figure 4. Gate Charge Characteristics

Figure 5. $R_{DS(on)}$ vs. V_{GS} Figure 6. $R_{DS(on)}$ vs. I_D

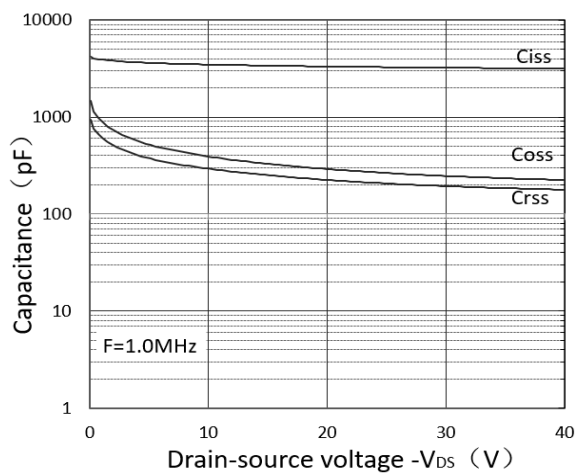


Figure 7. Capacitance Characteristics

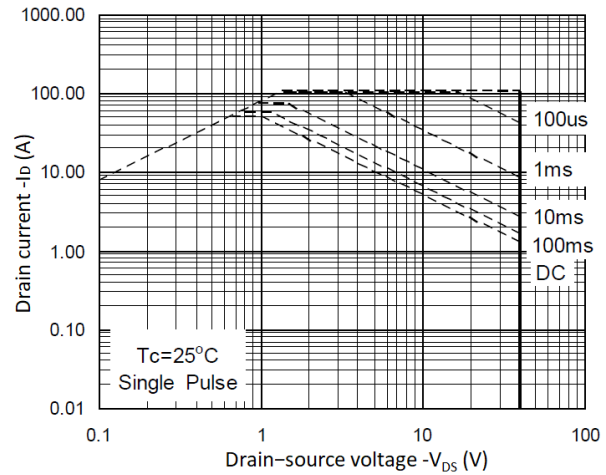


Figure 8. Safe Operating Area

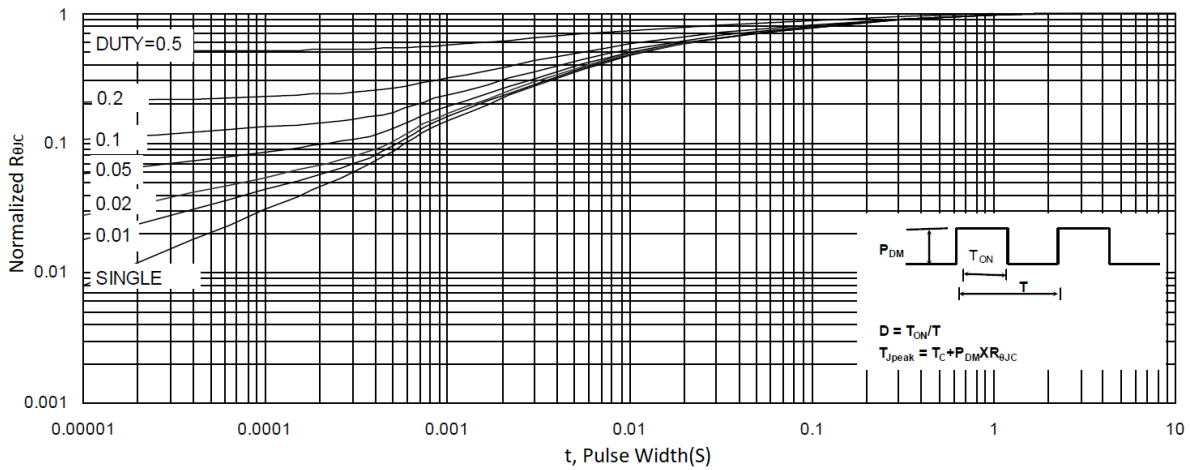


Figure 9. Normalized Maximum Transient Thermal Impedance

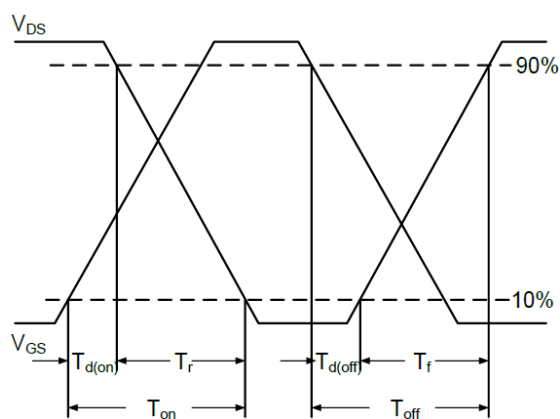
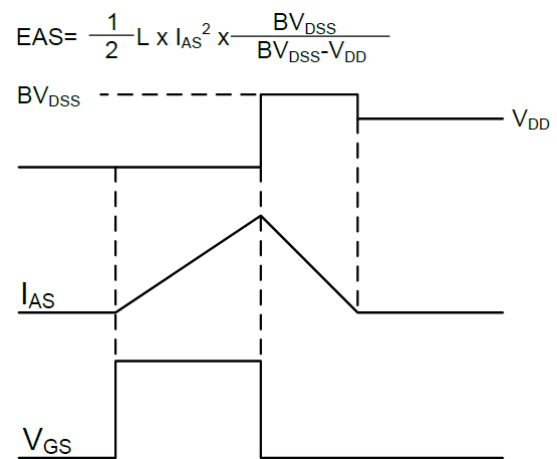
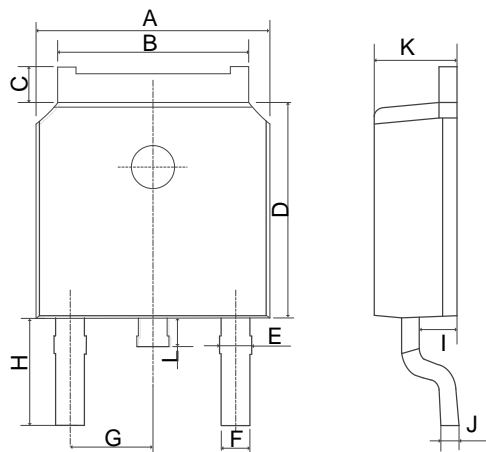


Figure 10. Switching Time Waveform

Figure 11. Unclamped Inductive Switching
Waveform

Mechanical Dimensions for TO-252



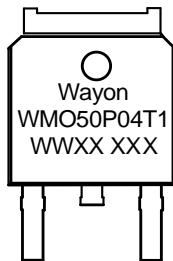
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00

Ordering Information

Part	Package	Marking	Packing method
WMO50P04T1	TO-252	WMO50P04T1	Tape and Reel

Marking Information



WMO50P04T1 = Device code

WWXX XXX= Manufacturing code

Contact Information

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